

Dear Editor and Reviewers,

We sincerely thank you for taking the time to review our manuscript “Iron’s impact on silicon solar cell execution: comprehensive modeling across diverse scenarios” (Ms. Ref. No.: MSB-S-24-02710). Your insightful comments and constructive suggestions have greatly helped us improve the quality of our work. We particularly appreciate your careful reading and thoughtful feedback, which have led to significant improvements in both the technical content and presentation clarity of our manuscript. We have carefully addressed all the comments and made corresponding revisions to the manuscript. Below we provide our detailed point-by-point responses to each comment. We hope the revised manuscript better meets your expectations and standards for publication in Materials Science and Engineering: B.

Response to Reviewer #1

Comment 1. *The author must explain the specific mechanisms you propose for the interaction between iron-related defects and other impurities in silicon solar cells? How might these interactions complicate the interpretation of photovoltaic performance metrics?*

Reply:

In general, interstitial iron is already mobile at room temperature and can interact with various impurities. Over 30 iron-related complexes have been identified in silicon, and nearly 25 energy levels associated with iron-related defects have been reported in the silicon bandgap across different studies [1, 2, 3]. For example, iron forms complexes with carbon, oxygen, hydrogen, sulfur, and other metal impurities, as well as with native defects in silicon. However, in terms of their impact on photovoltaic performance, two primary factors must be considered. First, the concentration of the relevant defects is crucial. It is widely recognized that in *p*-type silicon under equilibrium conditions, most iron impurity atoms pair with acceptors (e.g., boron in Si:B) [4, 1]. The concentration of other complexes is significantly lower, and detailed investigation of these complexes requires specialized sample preparation, such as additional doping with other expected complex components or irradiation to increase the concentration of native defects [5]. Further supporting this, several methods used to evaluate the total iron concentration in *p*-Si rely on breaking the FeB pair [6, 7, 8]. Second, the recombination activity of these centers must be considered, as it depends on the defect energy level relative to the Fermi level and the charge carrier capture cross-section. Interstitial iron and FeB pairs are among the most detrimental recombination-active impurities in *p*-Si [1, 9] in contrast to other iron-related defects. Notably, iron gettering by oxygen precipitates or structural defects increases carrier lifetime [10, 11]. In *n*-Si, Fe_i is not a recombination-active impurity due to the filling of its energy level. Reducing the impact of iron through gettering during phosphorus diffusion [10, 11, 12] or the formation of a passivating layer [13] is well-established and used in the solar cell industry.

Thus, our assumption that the primary influence of iron impurities in the *p*-regions of a solar cell on photoelectric parameters is due to Fe_iB_{Si} pairs and Fe_i is fully justified. Furthermore, we emphasize that this paper focuses on the relative changes in parameters during Fe_iB_{Si} ⇌ Fe_i + B_{Si} transformation, which enables the isolation of these specific defects’ contributions.

This answer is incorporated in the revised text on page 5, two last paragraph in Section 2.1. Simulation Details.

Comment 2. *The author should give the transient nature of defect dynamics, how do you assess the long-term stability of silicon solar cells in the presence of iron contamination? What experimental approaches would you recommend to study the aging effects of these defects over time?*

Reply:

Interstitial iron atoms exhibit high mobility in silicon [1]. For example, the characteristic time required for FeB pair formation, which depends on the diffusion coefficient of Fe_i, is given by the following expression [14, 15, 16]:

$$\tau = 5.7 \times 10^5 \frac{\text{s}}{\text{K cm}^3} \times \frac{T}{N_B} \exp\left(\frac{0.65}{kT}\right). \quad (1)$$

where N_B is the doping level.

That is, at room temperature, the formation of an equilibrium concentration of FeB pairs is completed within 24 hours, while at $T = 340$ K, the τ is approximately 10 minutes. Therefore, iron contamination is not a determining factor in the long-term stability of silicon solar cells, unlike sodium atoms, which are considered one of the primary contributors to potential-induced degradation [17].

The information on the characteristic time of FeB pair formation has been added to the revised manuscript (page 5, last paragraph in Section 2.2.).

The measurements were carried over the temperature range of 300-340 K. The sample temperature was driven by a thermoelectric cooler controlled by an STS-21 sensor and maintained constant by a PID algorithm embedded in the software that serves the experimental setup. **Notably, the characteristic time for FeB pair recovery after the cessation of illumination is approximately 13,000 seconds at 300 K and only 600 seconds at 340 K [14, 15]. These limitations affect the measurement duration at high temperatures, and the experiments accounted for them.**

Comment 3. *An Author should provide a theoretical framework for understanding how the temperature range you studied (290 K to 340 K) influences the activation energy of iron-related defects? How might this affect the performance of solar cells in varying environmental conditions?*

Reply:

Initially, we note that the selected temperature range reflects the realistic operating conditions of most silicon solar cells. In our calculations, we accounted for the temperature dependencies of both silicon properties — including bandgap, the effective density of states; effective masses, thermal velocities and mobilities of charge carriers; Auger and band-to-band recombination coefficients, and light absorption values — and defect parameters, such as energy level positions within the bandgap and electron and hole capture cross-sections. Additionally, we considered the temperature dependence of the equilibrium concentration ratio of Fe_i and FeB. Specifically, the primary effect of increasing temperature on iron-related defects is the rise in the relative equilibrium concentration of interstitial iron atoms and the change in the charge carrier capture cross-section of each defect.

Accounting for all the above factors in the modeling process suggests that the results presented in this work accurately reflect the impact of both defects and defect parameter variation on solar cell performance under varying environmental conditions, including temperature, illumination type, and intensity.

Details on how temperature dependencies were accounted for in the simulation can be found on page 3, last two paragraphs

As can be seen from Table 1, calculations spanned a broad range of temperatures and base doping levels. Therefore, to improve the accuracy of the calculations when inputting the initial parameters into SCAPS, **temperature and concentration (where applicable) dependencies of the following silicon parameters were taken into account:**

- bandgap according to Passler [18];
- doping induced bandgap narrowing according to Yan & Cuevas [19];
- effective density of states at conduction and valence band and intrinsic carrier concentration according to Couderc et al. [20];
- thermal carrier velocities according to Green [21];
- free carrier effective masses according to O'Mara et al. [22];
- carrier mobilities according to Klaassen's theory [23];

The values of surface recombination coefficients were considered equal to the thermal velocities of carriers [24]. The calculations addressed recombination processes within the structural volume, incorporating both intrinsic recombination and Shockley-Read-Hall (SRH) recombination at iron-related defects. In the first case, processes of band-to-band radiation recombination were considered (where the calculation of the corresponding coefficient included the fraction of radiatively emitted photons reabsorbed via band-to-band processes according to Niewelt et al.[25]) and Auger recombination (where the coefficients considered the effect of Coulomb enhancement [26] and **temperature dependence** [27]).

and page 4, 3rd and 4th paragraph from the top

Case 2. Iron atoms predominantly form pairs with acceptors, $[\text{Fe}_i\text{B}_s] \gg [\text{Fe}_i]$, but the exact concentration ratio depends on the position of the Fermi level and temperature [28, 29] and varies from point to point within the solar cell. Further details about calculation of the concentration profiles of Fe_iB_s and Fe_i are provided in [30, 31]. This case corresponds to prolonged storage of the structure in darkness or under conditions of low-intensity ($< 0.01 \text{ J cm}^{-2}$ [32]) illumination.

During the calculations, it was assumed that Fe_i forms a single donor level, while the Fe_iB_s pair has a trigonal configuration and acts as an amphoteric defect. We obtained defect parameters, including energy level positions within the bandgap, electron and hole capture cross-sections, and their temperature dependencies, based on data from relevant studies [33, 1, 34].

Comment 4. An Author mentioned the application of principal component analysis in evaluating impurity levels. Could you elaborate on how this technique was implemented in your study and its effectiveness in distinguishing between different types of impurities?

Reply:

Comment 5. Your paper discusses the influence of doping levels on the response of solar cells to iron contamination. Author should explain how varying the doping concentration affects the sensitivity of photovoltaic parameters to iron presence through the reference: Augmented photovoltaic performance of Cu/Ce-(Sn: Cd)/n-Si Schottky barrier diode utilizing dual-doped Ce-(Sn: Cd) thin films.

Reply:

The primary reason doping concentration N_B influences the sensitivity of photovoltaic parameters to iron presence is that the N_B determines the Fermi level E_F position. In turn, the rate of Shockley-Read-Hall recombination — and consequently, variations in photovoltaic parameters due to iron impurities — depends on the relative positioning of E_F concerning the Fe_iB_s and Fe_i levels. Additionally, the equilibrium ratio of Fe_iB_s and Fe_i concentrations is also determined by the Fermi level position [28, 29]. Therefore, N_B affects the number of defects that change their state due to the complete dissociation of Fe_iB_s pairs, leading to corresponding relative changes in photovoltaic parameters analyzed in this study. Besides, the N_B concentration also affects the SCR depth (see Fig. 4 in manuscript). The ratio of different charge states for both interstitial iron atoms and iron-boron pairs differs between the SCR and the bulk of the base, leading to distinct SRH recombination rates and variations in photovoltaic conversion efficiency for structures with different doping levels. Furthermore, according to Klaassen's model [23], the concentration of ionized impurities influences charge carrier mobility and, consequently, the diffusion coefficient D_n , diffusion length L_n , and photoelectric conversion efficiency (see Eqs. (4), (5), and (7) in the manuscript). However, the effect of N_B via D_n and L_n is significantly weaker than its influence through E_F and SCR depth variations. Minor effects are expected as well due to both bandgap narrowing and changes in light absorption by free carriers with varying doping levels. The impact of doping level on photovoltaic parameters has been studied in heterojunction [35], thin-film [36], and perovskite [37] solar cells. Moreover, it has been shown [36] that doping concentration variations affect other barrier structure parameters, such as saturation current and ideality factor.

This answer is incorporated in the text on page 4, paragraph 4, line 1-2. Reference is included in the revised manuscript (references 1)

...while the presence of the acceptor state Fe_iB_s causes the carrier lifetime to be doping-dependent under low injection conditions [FeB:Schmidt].

The relationship between N_B and E_F is the key factor in the influence of doping level on the sensitivity of photovoltaic parameters to iron presence. Specifically, the rate of SRH recombination — and consequently, variations in photovoltaic parameters due to iron impurities — depends on the relative positioning of E_F concerning the Fe_iB_s and Fe_i levels. Additionally, the equilibrium ratio of Fe_iB_s and Fe_i concentrations is also determined by the Fermi level position [FeB:kinetic,MurphyJAP2011]. Therefore, N_B affects the number of defects that change their state due to the complete dissociation of Fe_iB_s pairs, leading to corresponding

relative changes in photovoltaic parameters analyzed in this study. Besides, the N_B concentration also affects the SCR depth (see Fig. 4). The ratio of different charge states for both interstitial iron atoms and iron-boron pairs differs between the SCR and the bulk of the base, leading to distinct SRH recombination rates and variations in photovoltaic conversion efficiency for structures with different doping levels. Furthermore, according to Klaassen's model [KLAASSEN953], the concentration of ionized impurities influences charge carrier mobility and, consequently, the diffusion coefficient D_n , diffusion length L_n , and photoelectric conversion efficiency (see Eq. (4)). However, the effect of N_B via D_n and L_n is significantly weaker than its influence through E_F and SCR depth variations. Minor effects are expected as well due to both bandgap narrowing and changes in light absorption by free carriers with varying doping levels. The impact of doping level on photovoltaic parameters has been studied in heterojunction [8], thin-film [10], and perovskite [6] solar cells. Moreover, it has been shown [10] that doping concentration variations affect other barrier structure parameters, such as saturation current and ideality factor.

Comment 6. *In your findings, Author mentions that changes in short-circuit current under monochromatic illumination are the most reliable for estimating iron concentration. An author should provide more details on the methodology used to derive this conclusion and any potential limitations of this approach?*

Reply:

Comment 7. *An Author must improve the introduction section in the application part through the recent references CuO-La2O3 Composite-Enabled MIS Schottky Barrier Diodes: A Novel Approach to Optoelectronic Device Diversification; Enhancing photovoltaic applications through precipitating agents in ITO/CIS/CeO2/Al heterojunction solar cell; Manifestation on the choice of a suitable combination of MIS for proficient Schottky diodes for optoelectronics applications: A comprehensive review.*

[38, 39, 40]

We sincerely thank the Reviewer for suggesting the inclusion of recent references (cited as References 2, 3, and 9 in the revised manuscript). Below, we present an improved version of the 1st paragraph of Introduction.

The necessity for renewable energy sources to meet the growing global demand for sustainable and environmentally friendly energy alternatives has become evident. Among the wide range of renewable energy sources, sunlight is the cleanest, safest, and most abundant source for use in sustainable energy to support economic growth [1]. The utilization of solar energy heavily depends on the use of photovoltaic cells. The development of next-generation solar cells is primarily driven by the search for novel materials suitable for their fabrication. Particular attention is given to exploring the potential use of composites and nanoparticles (e.g., Cu-La-based systems [2], cerium oxide, and copper indium sulfate [3]), MAX phases [4,5], and chalcogenides (such as GeSe, MoSe₂, Sb₂Se₃, and SnSe as hole transport materials [6] or SnS₂ and WS₂ as electron transport materials [7]), as well as metal silicides (e.g., FeSi₂ as an absorber layer [8]). These studies cover a broad range of materials [9], with the primary goal of developing highly efficient and cost-effective photovoltaic devices. Frequently, these novel materials are integrated with silicon in solar cells [8,10]. However, it is worth noting that traditional silicon-based devices continue to play a dominant role in the photovoltaic market [11,12].

Reply:

Response to Reviewer #2

Comment 1. *The abstract section should be more informative.*

Reply:

Comment 2. *The novelty of the work is missing in the introduction. Authors should explain what are the key advantages of iron's impact on silicon solar cell?*

Reply:

Comment 3. *Authors should improve the image quality of all figures.*

Reply:

Comment 4. Author should explain how does the band alignment affect the overall performance of the solar cell?

Reply:

Comment 5. What are the primary sources of iron contamination in silicon used for solar cells?

Reply:

Comment 6. What role do recombination centers created by iron play in the modeling of solar cell performance?

Reply:

Comment 7. Author should discuss and cited recent Si based solar cell in the revised manuscript: DOI : 10.1016/j.mseb.2024.117360, DOI : 10.1016/j.mseb.2023.117141, DOI : 10.1016/j.mseb.2024.117817, DOI : 10.1007/s42247-024-00821-y, DOI : 10.1016/j.inoche.2024.112785

Reply:

We sincerely appreciate the reviewer's valuable suggestion. Most of the recommended works are highly relevant, and we have cited them in multiple sections of the manuscript. Advised articles are referenced as References 8, 4, 6, 7, and 5 in the revised version.

So, we discuss and cited suggested papers in the Introduction, first paragraph

The necessity for renewable energy sources to meet the growing global demand for sustainable and environmentally friendly energy alternatives has become evident. Among the wide range of renewable energy sources, sunlight is the cleanest, safest, and most abundant source for use in sustainable energy to support economic growth [1]. The utilization of solar energy heavily depends on the use of photovoltaic cells. The development of next-generation solar cells is primarily driven by the search for novel materials suitable for their fabrication. Particular attention is given to exploring the potential use of composites and nanoparticles (e.g., Cu-La-based systems [2], cerium oxide, and copper indium sulfate [3]), MAX phases [4,5], and chalcogenides (such as GeSe, MoSe₂, Sb₂Se₃, and SnSe as hole transport materials [6] or SnS₂ and WS₂ as electron transport materials [7]), as well as metal silicides (e.g., FeSi₂ as an absorber layer [8])

on page 3, first paragraph from the top

Despite its one-dimensional modeling approach, SCAPS is extensively used for modeling various types of solar cells [6,7,8, Joshi2024, Ravidas2024, Liu2024, You2023] in general and for investigating the effects of defects on their performance [6,8, AitAbdelkadir2023, Liang2024, SCAPSDefect3] in particular.

on page 4, last paragraph

Impact of change of iron defects was investigated as a function of temperature from 290 K to 340 K, base depth from 180 μm to 380 μm , base doping level from 10^{15} cm^{-3} to 10^{17} cm^{-3} , and total impurity iron atom concentration from 10^{10} cm^{-3} to 10^{14} cm^{-3} . It is worth noting that investigating the effects of doping density, defect density, temperature, and active layer thickness on photovoltaic parameters is a well-established practice [6,7,8]. For each illumination scenario, calculations were carried out with 11 different temperature values and 5 base depth values, evenly distributed within the specified ranges.

on page 7, 3rd paragraph from the bottom

However, the effect of N_B via D_n and L_n is significantly weaker than its influence through E_F and SCR depth variations. Minor effects are expected as well due to both bandgap narrowing and changes in light absorption by free carriers with varying doping levels. The impact of doping level on photovoltaic parameters has been studied in heterojunction [8], thin-film [10], and perovskite [6] solar cells. Moreover, it has been shown [10] that doping concentration variations affect other barrier structure parameters, such as saturation current and ideality factor.

on page 7, 4th paragraph from the top

- At low boron concentrations ($N_B < 10^{16} \text{ cm}^{-3}$), the dependence of ϵFF on N_{Fe} is notably non-linear. Within the used concentration range, two regions of decrease and two regions of increase in ϵFF are observed. A similar relationship between the fill factor and defect concentration was observed in BaZrSe₃-based perovskite solar cells [6];

Comment 8. *How does the modeling in this study contribute to the design of processes for impurity control in silicon?*

Reply:

Comment 9. *State the main findings in the conclusions.*

Reply:

References

- [1] A. A. Istratov, H. Hieslmair, E. Weber, Iron and its complexes in silicon, *Appl. Phys. A: Mater. Sci. Process.* 69 (1999) 13–44.
- [2] K. Gwozdz, V. Kolkovsky, Fe-related defects in si: Laplace deep-level transient spectroscopy studies, *Phys. Status Solidi A* 219 (2022) 2200139.
- [3] I. Jyothi, V. Janardhanam, H. Hong, C.-J. Choi, Current–voltage and capacitance–voltage characteristics of al schottky contacts to strained si-on-insulator in the wide temperature range, *Mater. Sci. Semicond. Process.* 39 (2015) 390–399.
- [4] L. Kimerling, J. Benton, Electronically controlled reactions of interstitial iron in silicon, *Physica B+C* 116 (1983) 297–300.
- [5] C. K. Tang, L. Vines, V. P. Markevich, B. G. Svensson, E. V. Monakhov, Divacancy-iron complexes in silicon, *J. Appl. Phys.* 113 (2013) 044503.
- [6] G. Zoth, W. Bergholz, A fast, preparation-free method to detect iron in silicon, *J. Appl. Phys.* 67 (1990) 6764–6771.
- [7] S. Herlufsen, D. Macdonald, K. Bothe, J. Schmidt, Imaging of the interstitial iron concentration in crystalline silicon by measuring the dissociation rate of iron–boron pairs, *Phys. Status Solidi RRL* 6 (2012) 1–3.
- [8] O. Olikh, V. Kostilyov, V. Vlasuk, R. Korkishko, Y. Olikh, R. Chupryna, Features of FeB pair light-induced dissociation and repair in silicon n+-p-p+ structures under ultrasound loading, *J. Appl. Phys.* 130 (2021) 235703.
- [9] T. Mchedlidze, L. Scheffler, J. Weber, M. Herms, J. Neusel, V. Osinniy, C. Moller, K. Lauer, Local detection of deep carrier traps in the pn-junction of silicon solar cells, *Appl. Phys. Lett.* 103 (2013) 013901.
- [10] J. Schön, H. Habenicht, M. C. Schubert, W. Warta, Understanding the distribution of iron in multicrystalline silicon after emitter formation: Theoretical model and experiments, *J. Appl. Phys.* 109 (2011) 063717.
- [11] V. Vähänissi, A. Haarahiltunen, H. Talvitie, M. Yli-Koski, H. Savin, Impact of phosphorus gettering parameters and initial iron level on silicon solar cell properties, *Progress in Photovoltaics: Research and Applications* 21 (2013) 1127–1135.
- [12] V. Vähänissi, H. S. Laine, Z. Liu, M. Yli-Koski, A. Haarahiltunen, H. Savin, Full recovery of red zone in p-type high-performance multicrystalline silicon, *Sol. Energ. Mat. Sol.* 173 (2017) 120–127.
- [13] T. Mchedlidze, C. Möller, K. Lauer, J. Weber, Evolution of iron-containing defects during processing of si solar cells, *J. Appl. Phys.* 116 (2014) 245701.
- [14] C. Möller, T. Bartel, F. Gibaja, K. Lauer, Iron-boron pairing kinetics in illuminated p-type and in boron/phosphorus co-doped n-type silicon, *J. Appl. Phys.* 116 (2014) 024503.
- [15] N. Khelifati, H. S. Laine, V. Vähänissi, H. Savin, F. Z. Bouamama, D. Bouhafs, Dissociation and formation kinetics of iron–boron pairs in silicon after phosphorus implantation gettering, *Phys Status Solidi A* 216 (2019) 1900253.
- [16] J. Tan, D. Macdonald, F. Rougieux, A. Cuevas, Accurate measurement of the formation rate of iron–boron pairs in silicon, *Semicond Sci. Technol.* 26 (2011) 055019.
- [17] S. Yamaguchi, B. B. Van Aken, A. Masuda, K. Ohdaira, Potential-induced degradation in high-efficiency n-type crystalline-silicon photovoltaic modules: A literature review, *Sol. RRL* 5 (2021) 2100708.
- [18] R. Pässler, Dispersion-related description of temperature dependencies of band gaps in semiconductors, *Phys. Rev. B* 66 (2002) 085201.
- [19] D. Yan, A. Cuevas, Empirical determination of the energy band gap narrowing in p⁺ silicon heavily doped with boron, *J. Appl. Phys.* 116 (2014) 194505.
- [20] R. Couderc, M. Amara, M. Lemiti, Reassessment of the intrinsic carrier density temperature dependence in crystalline silicon, *J. Appl. Phys.* 115 (2014) 093705.
- [21] M. A. Green, Intrinsic concentration, effective densities of states, and effective mass in silicon, *J. Appl. Phys.* 67 (1990) 2944–2954.
- [22] W. O'Mara, R. Herring, L. Hant, *Handbook of semiconductor silicon technology*, Noyes Publications, New Jersey, USA, 1990.
- [23] D. Klaassen, A unified mobility model for device simulation — I. model equations and concentration dependence, *Solid-State Electron.* 35 (1992) 953–959.
- [24] A. Fell, K. R. McIntosh, P. P. Altermatt, G. J. M. Janssen, R. Stangl, A. Ho-Baillie, H. Steinkemper, J. Greulich, M. Müller, B. Min, K. C. Fong, M. Hermle, I. G. Romijn, M. D. Abbott, Input parameters for the simulation of silicon solar cells in 2014, *IEEE J. Photovolt.* 5 (2015) 1250–1263.
- [25] T. Niewelt, B. Steinhauser, A. Richter, B. Veith-Wolf, A. Fell, B. Hammann, N. Grant, L. Black, J. Tan, A. Youssef, J. Murphy, J. Schmidt, M. Schubert, S. Glunz, Reassessment of the intrinsic bulk recombination in crystalline silicon, *Sol. Energ. Mat. Sol.* 235 (2022) 111467.
- [26] L. E. Black, D. H. Macdonald, On the quantification of Auger recombination in crystalline silicon, *Sol. Energ. Mat. Sol.* 234 (2022) 111428.
- [27] P. P. Altermatt, J. Schmidt, G. Heiser, A. G. Aberle, Assessment and parameterisation of Coulomb-enhanced Auger recombination coefficients in lowly injected crystalline silicon, *J. Appl. Phys.* 82 (1997) 4938–4944.
- [28] W. Wijaranakula, The reaction kinetics of iron–boron pair formation and dissociation in p-type silicon, *J. Electrochem. Soc.* 140 (1993) 275–281.
- [29] J. D. Murphy, K. Bothe, M. Olmo, V. V. Voronkov, R. J. Falster, The effect of oxide precipitates on minority carrier lifetime in p-type silicon, *J. Appl. Phys.* 110 (2011) 053713.
- [30] O. Olikh, O. Lozitsky, O. Zavhorodnii, Estimation for iron contamination in si solar cell by ideality factor: Deep neural network approach, *Prog. Photovoltaics Res. Appl.* 30 (2022) 648–660.

- [31] O. Olikh, Relationship between the ideality factor and the iron concentration in silicon solar cells, *Superlattices Microstruct.* 136 (2019) 106309.
- [32] D. H. Macdonald, L. J. Geerligs, A. Azzizi, Iron detection in crystalline silicon by carrier lifetime measurements for arbitrary injection and doping, *J. Appl. Phys.* 95 (2004) 1021–1028.
- [33] F. E. Rougieux, C. Sun, D. Macdonald, Determining the charge states and capture mechanisms of defects in silicon through accurate recombination analyses: A review, *Sol. Energy Mater. Sol. Cells* 187 (2018) 263 – 272.
- [34] B. B. Paudyal, K. R. McIntosh, D. H. Macdonald, Temperature dependent electron and hole capture cross sections of iron-contaminated boron-doped silicon, in: 2009 34th IEEE Photovoltaic Specialists Conference (PVSC), pp. 001588–001593.
- [35] B. Sultana, M. Ferdous Rahman, A. Chandra Roy, M. Masum Mia, M. Al Ijajul Islam, A. Irfan, A. Rasool Chaudhry, M. Dulal Haque, A novel design and optimization of si based high performance double absorber heterojunction solar cell, *Materials Science and Engineering: B* 304 (2024) 117360.
- [36] T. Akila, P. Gayathri, G. Alan Sibu, V. Balasubramani, H. Al-Lohedan, D. M. Al-Dhayan, Augmented photovoltaic performance of cu/ce-(sn:cd)/n-si schottky barrier diode utilizing dual-doped ce-(sn:cd) thin films, *Opt. Mater.* 149 (2024) 115133.
- [37] M. Masum Mia, M. Faruk Hossain, M. Rahman, N. Badi, A. Irfan, M. Ferdous Rahman, Unveiling the impact of se based htm on bazrse3 perovskites solar cell and improving the theoretical efficiency above 32%, *Materials Science and Engineering: B* 311 (2025) 117817.
- [38] M. J. Paul, R. Suresh, P. Gayathri, V. Balasubramani, K. M. Al-Anazi, M. A. Farah, CuO-Ia2o3 composite-enabled mis schottky barrier diodes: A novel approach to optoelectronic device diversification, *J. Inorg. Organomet. Polym. Mater.* (2024).
- [39] P. Gayathri, T. Akila, G. A. Sibu, M. Selvaraj, M. A. Assiri, P. matheswaran, V. Balasubramani, Enhancing photovoltaic applications through precipitating agents in ito/cis/ceo2/al heterojunction solar cell, *Inorg. Chem. Commun.* 168 (2024) 112866.
- [40] G. Alan Sibu, P. Gayathri, T. Akila, R. Marnadu, V. Balasubramani, Manifestation on the choice of a suitable combination of mis for proficient schottky diodes for optoelectronic applications: A comprehensive review, *Nano Energy* 125 (2024) 109534.